Darlington Transistors

multicomp PRO

NPN



BDW93B BDW94B BDW93C BDW94C 12 Amperes Darlington Complementary Silicon Power Transistors 45V - 100V 80W

PNP

Features

- · Designed for general-purpose amplifier and low speed switching applications
- Collector-Emitter sustaining voltage
- VCEO (sus) = 80V (Minimum) BDW93B, BDW94B = 100V (Minimum) - BDW93C, BDW94C
- Collector-Emitter saturation voltage V_{CE (sat)} = 2V (Maximum) at Ic = 5A
- · Monolithic construction with Built-in Base-Emitter shunt resistor

Maximum Ratings

Characteristic	Symbol	BDW93B BDW94B	BDW93C BDW94C	Unit	
Collector - Emitter Voltage	VCEO	80	100		
Collector - Base Voltage	Vсво	00	100	V	
Emitter - Base Voltage	Vebo	5			
Collector Current - Continuous - Peak	Іс Ісм	12 15		A	
Base Current	Ів	0.2			
Total Power Dissipation at Tc = 25°C Derate above 25°C	PD	80 0.64		W W/°C	
Operating and Storage Junction Temperature Range	Tj, Tstg	-65 to +150		°C	

Thermal Characteristics

Characteristic	Symbol	Maximum	Unit
Thermal Resistance Junction to case	Rejc	1.56	°C / W



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Electrical Characteristics (Tc = 25°C unless otherwise specified)

Characteristic	Symbol	Minimum	Maximum	Unit	
OFF Characteristics					
Collector - Emitter Sustaining Voltage (1) (Ic = 100mA, I _B = 25mH) BDW93B, BDW94B BDW93C, BDW94C	VCEO (sus)	80 100	-	V	
Collector Cut off Current (V _{CE} = 80V, I _B = 0) BDW93B, BDW94B BDW93C, BDW94C	ICEO	-	1	mA	
Collector-Base Cut off Current (VcB = Rated VcB, IE = 0)	Ісво	-	100	μA	
Emitter-Base Cut off Current $(V_{EB} = 5V, I_{C} = 0)$	Іево	-	2	mA	
ON Characteristics (1)					
DC Current Gain (Ic = 3A, VcE = 3V) (Ic = 5A, VcE = 3V) (Ic = 10A, VcE = 3V)	hfe	1,000 750 100	20,000	-	
Collector-Emitter Saturation Voltage (Ic = 5A, IB = 20mA) (Ic = 10A, IB = 100mA)	Vce (sat)	-	2 3		
Base-Emitter Saturation Voltage V (Ic = 5A, IB = 20mA) (Ic = 10A, IB = 100mA)	VBE (sat)	-	2.5 4	V	

(1) Pulse Test : Pulse Width = 300µs, Duty Cycle = 2%





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BDW93 Series NPN





BDW94 Series PNP



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Diagram



Dimensions	Minimum	Maximum
A	14.68	15.31
В	9.78	10.42
С	5.01	6.52
D	13.06	14.62
E	3.57	4.07
F	2.42	3.66
G	1.12	1.36

Dimensions	Minimum	Maximum
Н	0.72	0.96
I	4.22	4.98
J	1.14	1.38
K	2.2	2.97
L	0.33	0.55
М	2.48	2.98
0	3.7	3.9

Dimensions : Millimetres

Specification Table

Ic (AV) Maximum (A)	Vсео Maximum (V)	hFE Minimum at Ic = 5A	Ptot at 25°C (W)	Package	Туре	Part Number
12 80 100	80	80 750 100			NPN	BDW94B
	00		80	TO 220		BDW93B
	100		00	10-220	PNP	BDW93C
						BDW94C

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